NSN 5961-01-358-8557

Fiig: A110a0

Photo Semiconductor Device - Page 1 of 1



View Online at https://aerobasegroup.com/nsn/5961-01-358-8557 **Inclosure Material:** Metal and glass **Overall Length:** 0.235 inches **Terminal Length:** 0.500 inches **Overall Diameter:** 0.219 inches **Function For Which Designed:** Phototransistor **Mounting Method: Terminal Terminal Circle Diameter:** 0.100 inches **Semiconductor Material:** Silicon Voltage Rating In Volts Per Characteristic: 30.0 breakdown voltage, collector-to-emitter, base open and 7.0 breakdown voltage, emitter-to-base, collector open **Current Rating Per Characteristic:** 100.00 nanoamperes repetitive peak forward current peak **Terminal Type And Quantity:** 3 uninsulated wire lead Shelf Life: N/a **Unit Of Measure: Demilitarization:** No